

L Number	Hits	Search Text	DB	Time stamp
1	0	(laser near annealing) and intensity and profile and (control or memory)	USOCR	2004/11/05 13:30
2	0	(laser near annealing) and profile and (control or memory)	USOCR	2004/11/05 13:29
3	0	(laser near annealing) and intensity and profile	USOCR	2004/11/05 13:29
4	0	(laser near annealing) and intensity	USOCR	2004/11/05 13:30
5	289	(laser near annealing) and intensity and profile and (control or memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:30
6	55	((laser near annealing) and intensity and profile and (control or memory)) and (beam near profile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:32
7	55	((laser near annealing) and intensity and profile and (control or memory)) and (beam near profile)) and (semiconductor or transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:36
8	0	((laser near annealing) and intensity and profile and (control or memory)) and (beam near profile)) and (semiconductor or transistor)) and @ad<=2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:37
9	0	((laser near annealing) and intensity and profile and (control or memory)) and (beam near profile)) and (semiconductor or transistor)) and @ad<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:38